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(12) **United States Design Patent**
Majima et al.

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(54) **SEMICONDUCTOR DEVICE**

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- (73) Assignee: **ROHM CO., LTD.**, Kyoto (JP)
- (**) Term: **15 Years**
- (21) Appl. No.: **29/689,360**
- (22) Filed: **Apr. 29, 2019**
- (30) **Foreign Application Priority Data**

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- (51) **LOC (12) Cl.** **13-03**
- (52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**

USPC D10/80, 103; D13/110, 133, 139, 154, D13/173, 182; D14/217, 432, 433
 CPC H01L 20/4238; H01L 23/528; H01L 29/0696; H01L 29/1095; H01L 29/417; H01L 29/66068; H01L 29/1608; H01L 29/7395; H01L 29/7802; H01L 29/66325; H01L 29/66348; H01L 29/161; H01L 29/162; H01L 29/163; H01L 29/164; H01L 29/165; H01L 29/166; H01L 29/167; H01L 21/18; H01L 21/19; H01L 21/20; H01L 21/21; H01L 21/22; H01L 21/23; H01L 21/24; H01L 21/25; H01L 21/26; H01L 21/27; H01L 21/28; H01L 21/29; H01L 21/30

See application file for complete search history.

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(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. 1 is a front, bottom and right side perspective view of a semiconductor device showing our new design;

FIG. 2 is a front view thereof;

FIG. 3 is a top plan view thereof;

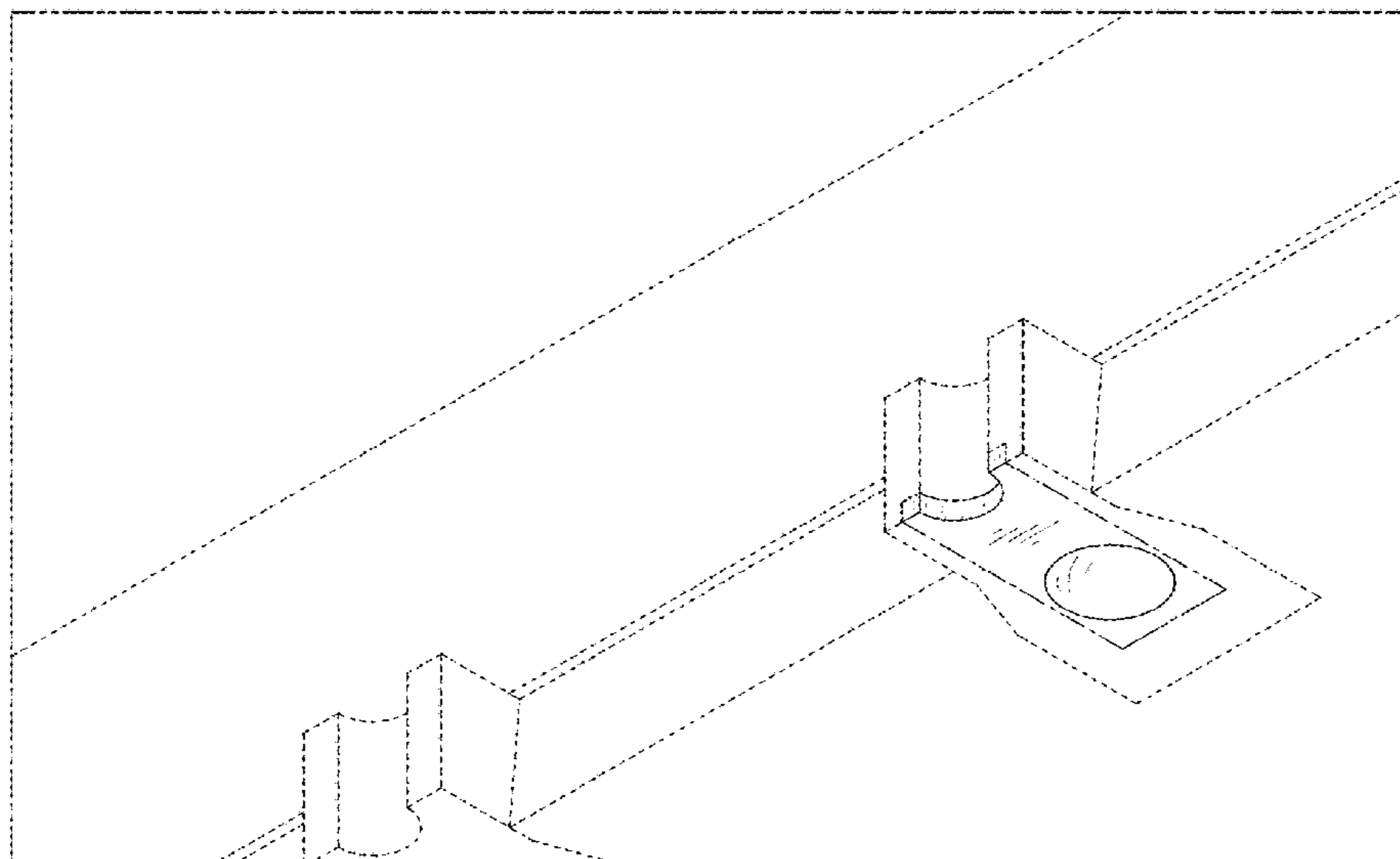
FIG. 4 is a bottom plan view thereof;

FIG. 5 is an enlarged view of a portion indicated by line 5-5 in FIG. 1; and,

FIG. 6 is an enlarged cross-sectional view taken along line 6-6 in FIG. 2 showing a portion indicated by lines 6-6 in FIG. 4.

The broken lines illustrate portions of the semiconductor device that form no part of the claimed design. The dash-dotted lines denote the boundary of the claim and form no part of the claimed design.

1 Claim, 6 Drawing Sheets



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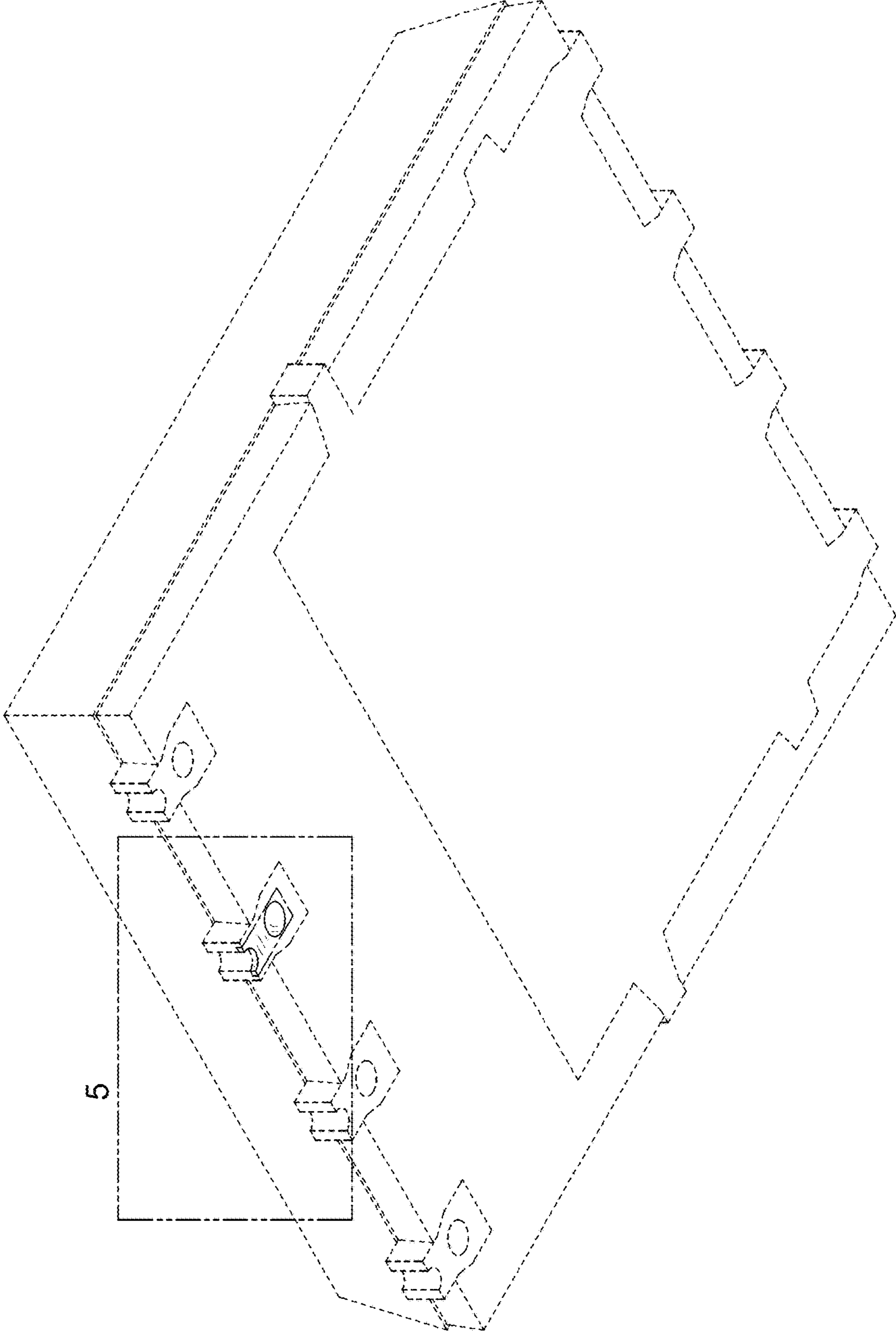


FIG.1

FIG.2

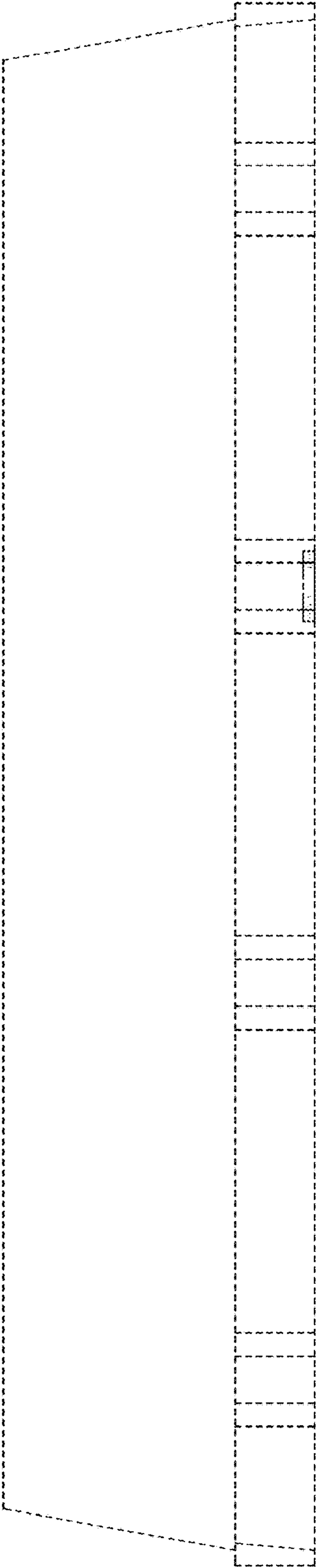


FIG.3

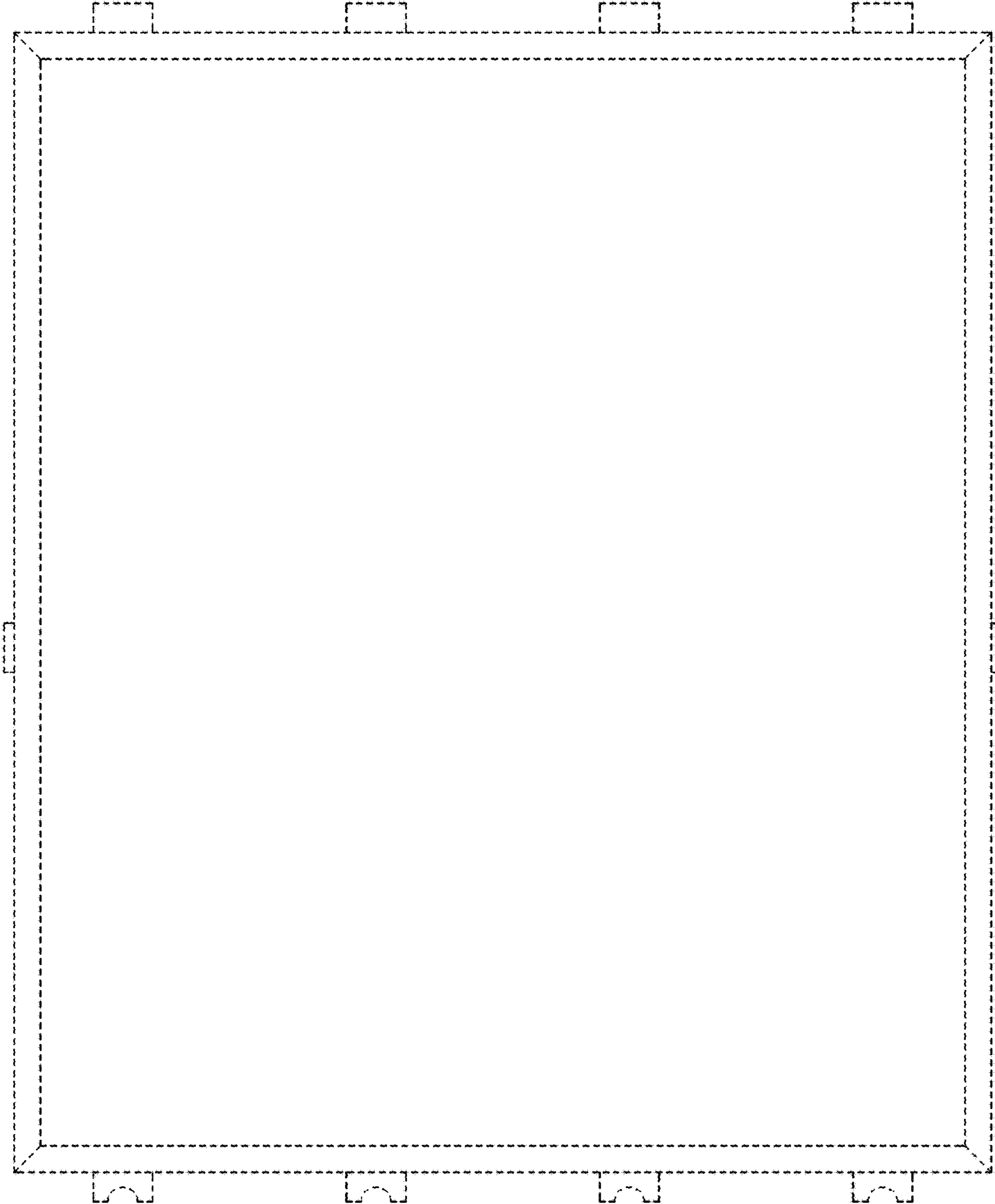
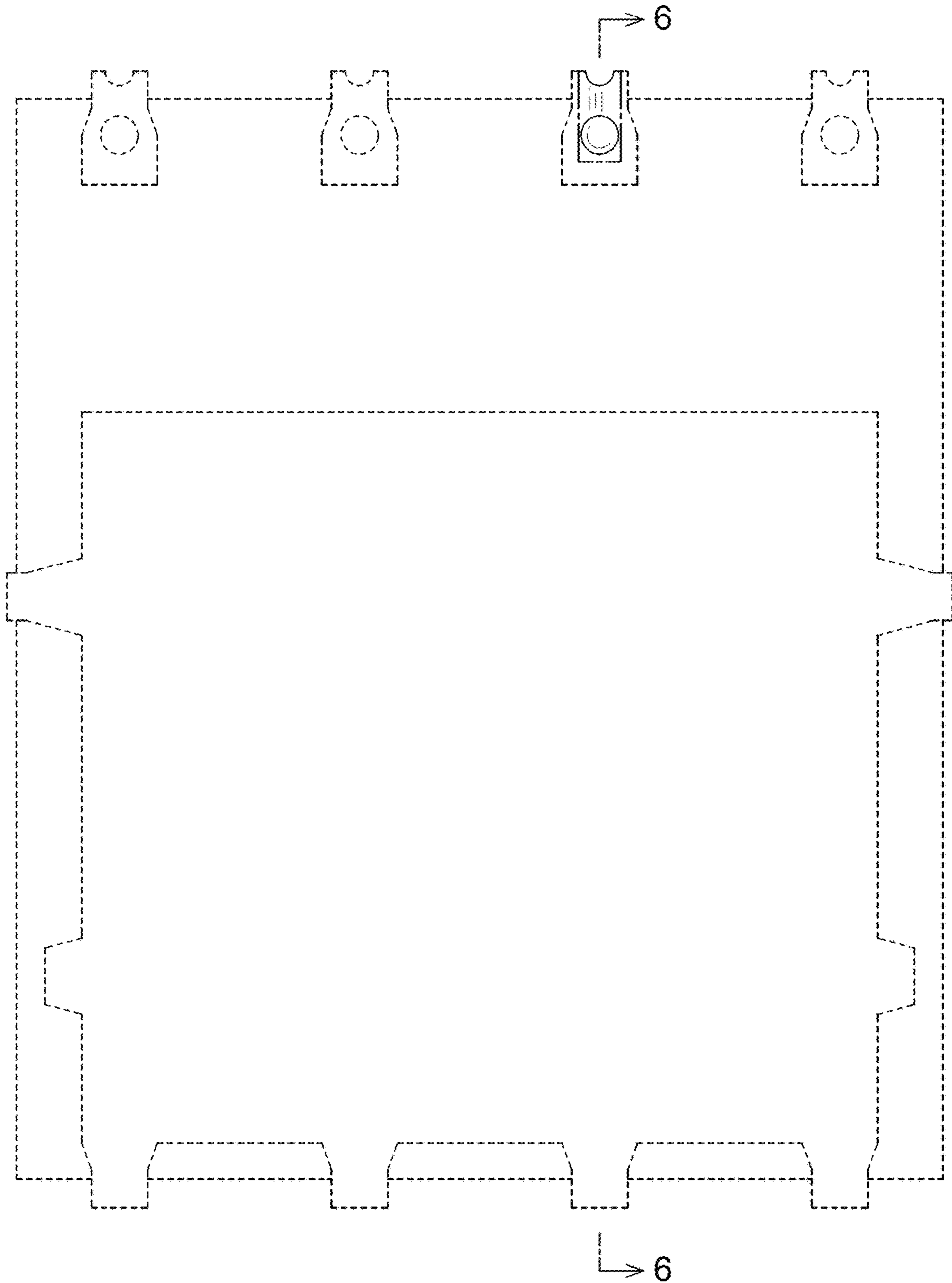


FIG.4



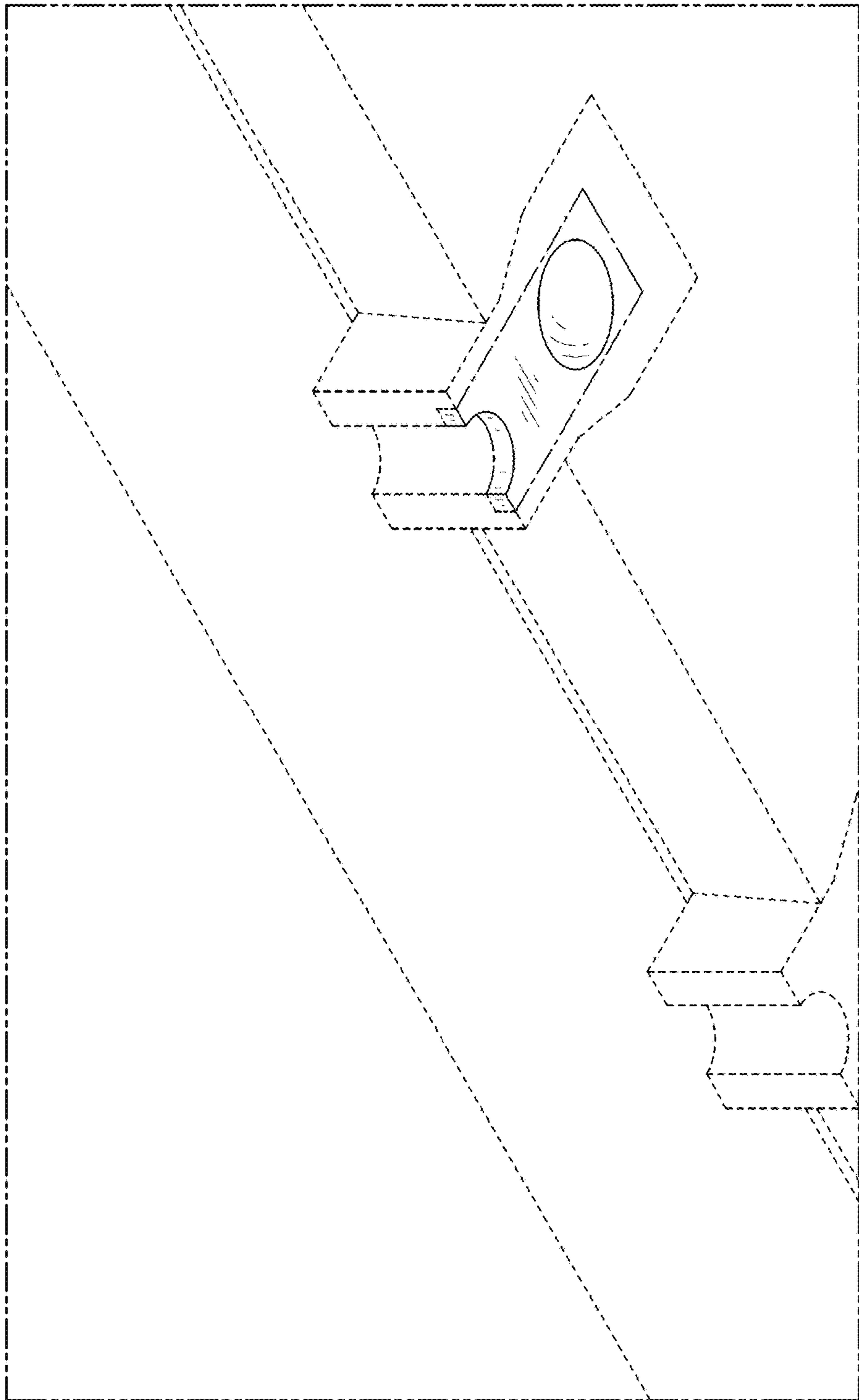


FIG. 5

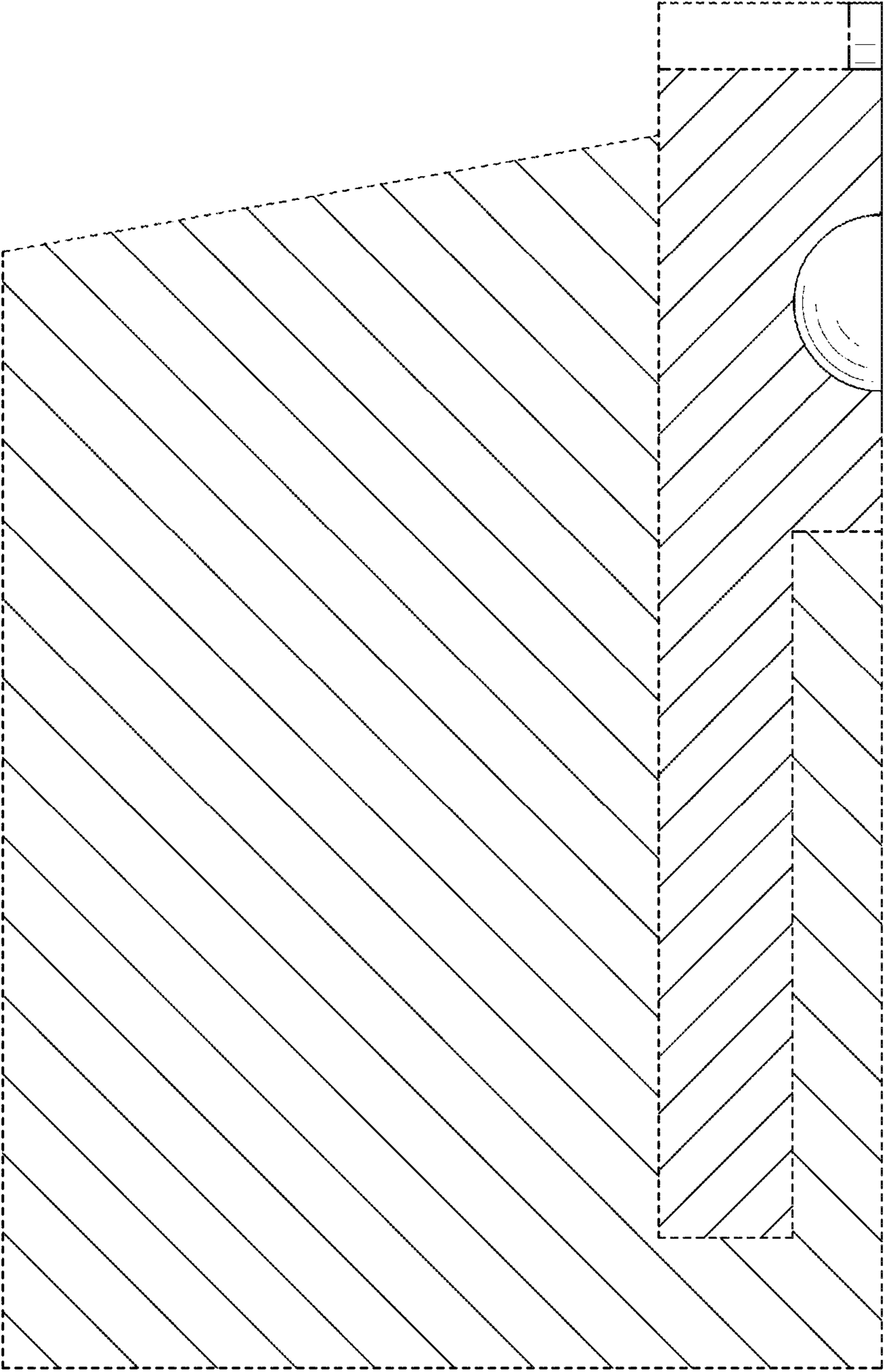


FIG.6